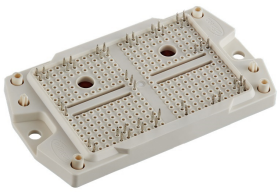
EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / NTC



Features

- Electrical features
  - V_{DSS} = 2000 V
  - I_{DN} = 60 A / I_{DRM} = 120 A
  - High current density
  - Low inductive design
- Mechanical features
  - Rugged mounting due to integrated mounting clamps
  - PressFIT contact technology
  - Integrated NTC temperature sensor

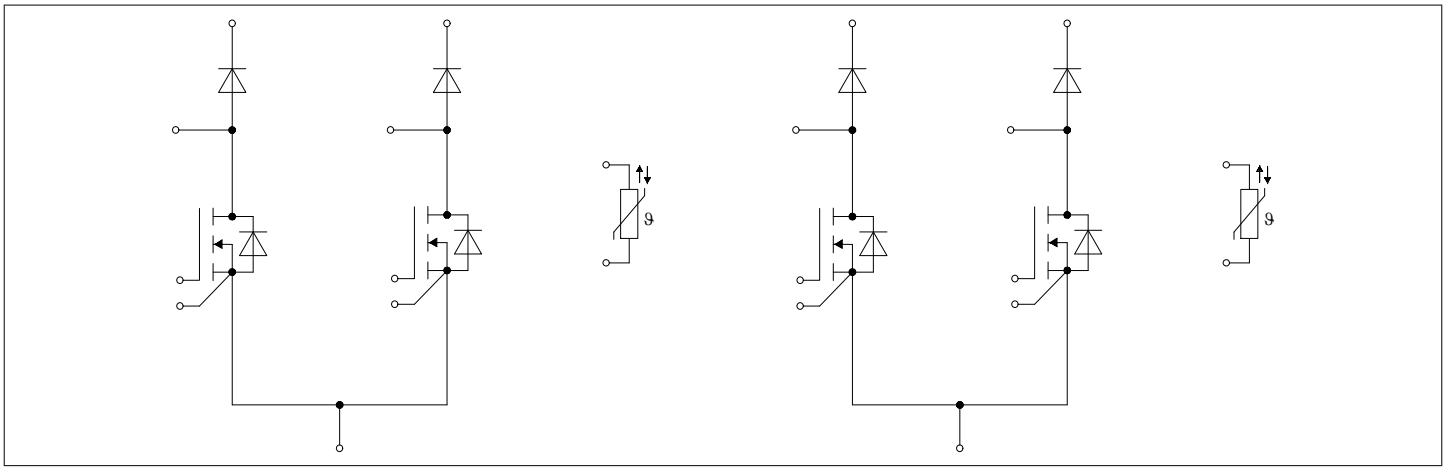
Potential applications

- Solar applications

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	3.2	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.4	mm
Creepage distance	d_{Creep}	terminal to terminal	10.2	mm
Clearance	d_{Clear}	terminal to heatsink	10.1	mm
Clearance	d_{Clear}	terminal to terminal	9.4	mm
Comparative tracking index	*CTI*		> 400	
Relative thermal index (electrical)	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				14		nH
Storage temperature	T_{stg}			-40		125	°C
Mounting torque for module mounting	*M*	- Mounting according to valid application note	M5, Screw	1.3		1.5	Nm
Weight	*G*				78		g

Note: The current under continuous operation is limited to 25 A rms per connector pin.

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	2000	V
Implemented drain current	I_{DN}			60	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 65 °C	50	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		120	A
Gate-source voltage, max. transient voltage	V_{GS}	*D* < 0.01		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		18	V
Off-state gate voltage	$V_{GS(off)}$		-3	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 60 A	V_{GS} = 18 V, T_{vj} = 25 °C		17.2	26.5	mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		36.6		
			V_{GS} = 18 V, T_{vj} = 175 °C		51.7		
Gate threshold voltage	$V_{GS(th)}$	I_D = 34 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V)		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 1200 V, V_{GS} = -3/18 V			0.234		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			3.8		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C		7.24		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.169		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.012		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 1200 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			154		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 2000 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.012	205	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 60 A, R_{Gon} = 1.6 Ω, V_{DD} = 1200 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		38.1		ns
			T_{vj} = 125 °C		38.1		
			T_{vj} = 175 °C		38.1		
Rise time (inductive load)	t_r	I_D = 60 A, R_{Gon} = 1.6 Ω, V_{DD} = 1200 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		26		ns
			T_{vj} = 125 °C		26		
			T_{vj} = 175 °C		26		
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 60 A, R_{Goff} = 2 Ω, V_{DD} = 1200 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		74.4		ns
			T_{vj} = 125 °C		81.5		
			T_{vj} = 175 °C		83.9		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Fall time (inductive load)	t_f	I_D = 60 A, R_{Goff} = 2 Ω, V_{DD} = 1200 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		16		ns
			T_{vj} = 125 °C		16.1		
			T_{vj} = 175 °C		17.1		
Turn-on energy loss per pulse	E_{on}	I_D = 60 A, V_{DD} = 1200 V, L_σ = 35 nH, V_{GS} = -3/18 V, R_{Gon} = 1.6 Ω, di/dt = 5 kA/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		1.5		mJ
			T_{vj} = 125 °C		1.5		
			T_{vj} = 175 °C		1.5		
Turn-off energy loss per pulse	E_{off}	I_D = 60 A, V_{DD} = 1200 V, L_σ = 35 nH, V_{GS} = -3/18 V, R_{Goff} = 2 Ω, dv/dt = 56.14 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.435		mJ
			T_{vj} = 125 °C		0.481		
			T_{vj} = 175 °C		0.529		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET			0.515		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: The body diode of CoolSiC™ Trench MOSFET cannot be used for polarity protection. An external diode is needed for this purpose.

The selection of positive and negative gate-source voltages impacts the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj\,op}$ > 150°C is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13

3 Body diode

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 60 A, V_{GS} = -3 V	T_{vj} = 25 °C		4.6	6.15	V
			T_{vj} = 125 °C		4.15		
			T_{vj} = 175 °C		4		

4 Diode, Boost

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	2000	V
Continuous DC forward current	I_F			40	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		80	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	90	A^2s
			T_{vj} = 175 °C	70	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 40 A	T_{vj} = 25 °C		1.50	1.85	V
			T_{vj} = 125 °C		2.17		
			T_{vj} = 175 °C		2.67		
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.685		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: $T_{vj\,op}$ > 150°C is allowed for operation at overload conditions for booster diode. For detailed specifications, please refer to AN 2021-13

5 NTC-Thermistor

Table 9 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2\text{-}1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2\text{-}1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2\text{-}1/(298{,}15\ K))]$		3433		K

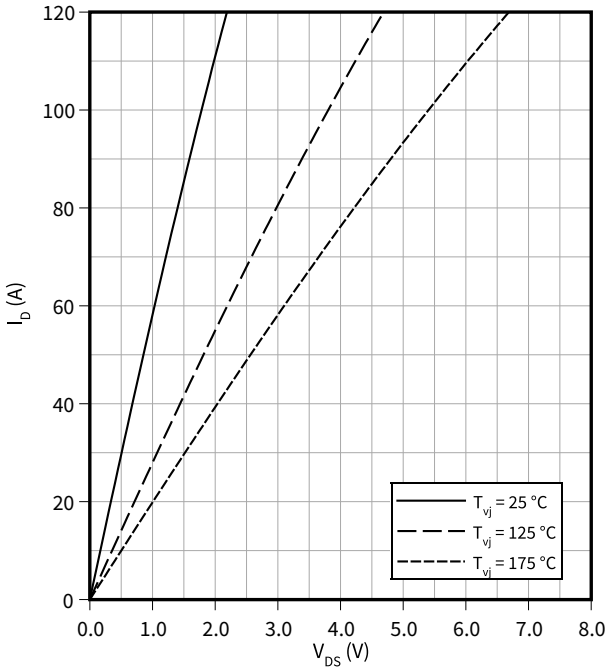
Note: Specification according to the valid application note.

6 Characteristics diagrams

Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

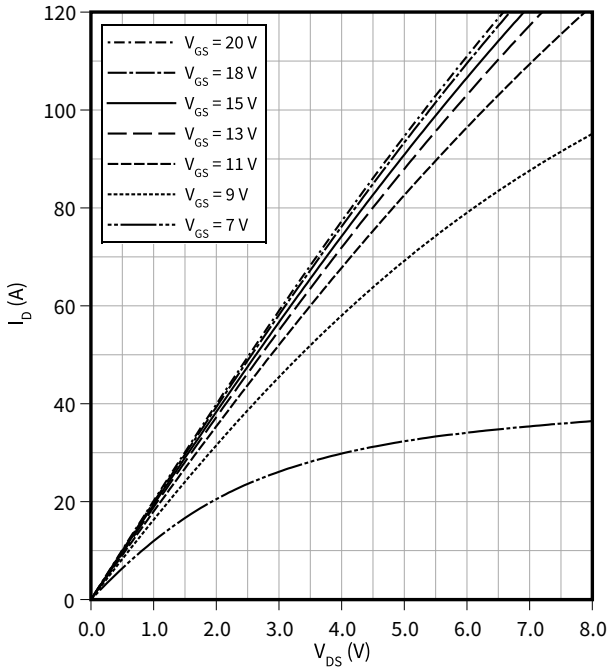
$V_{GS} = 18$ V



Output characteristic field (typical), MOSFET

$I_D = f(V_{DS})$

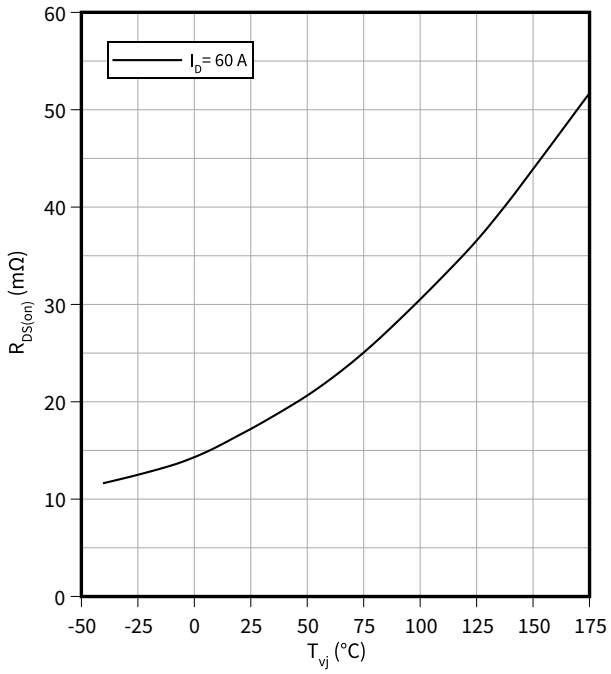
$T_{vj} = 175$ °C



Drain source on-resistance (typical), MOSFET

$R_{DS(on)} = f(T_{vj})$

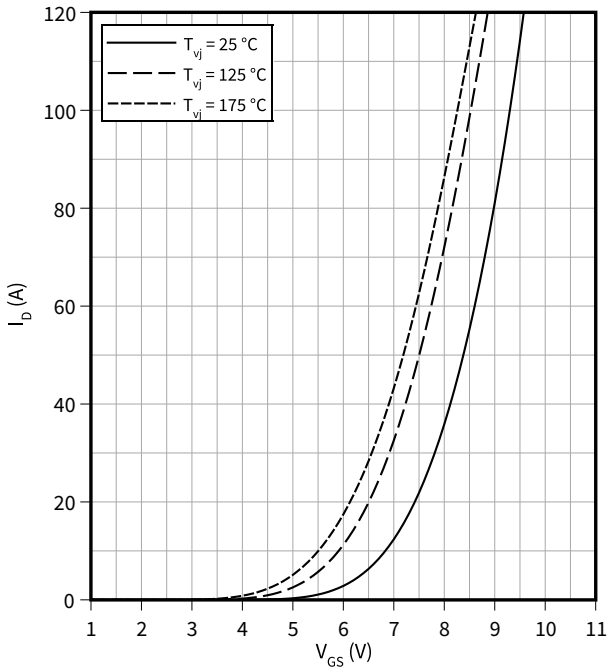
$V_{GS} = 18$ V



Transfer characteristic (typical), MOSFET

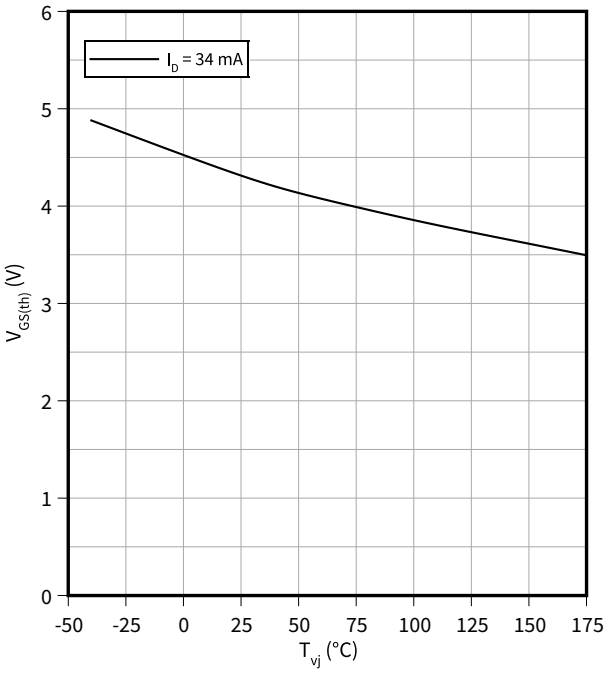
$I_D = f(V_{GS})$

$V_{DS} = 20$ V



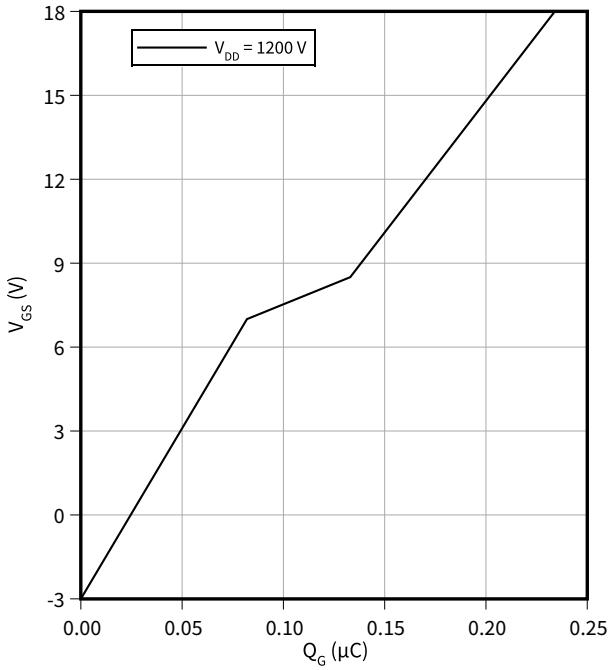
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



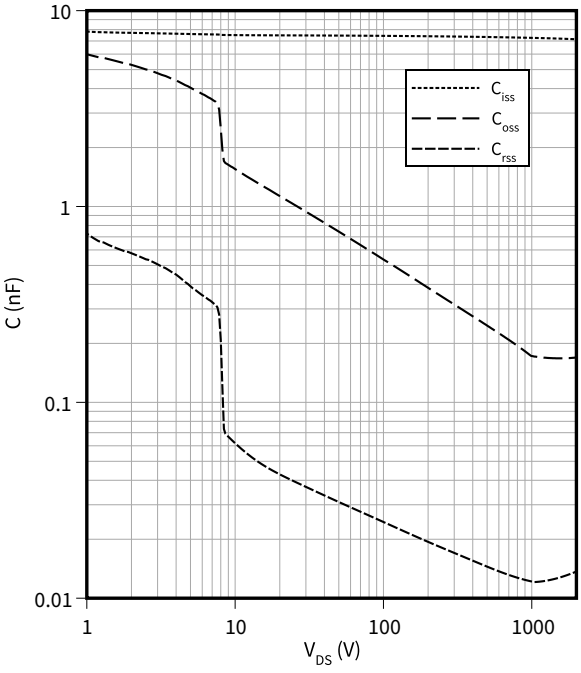
Gate charge characteristic (typical), MOSFET

$V_{GS} = f(Q_G)$
$I_D = 60$ A, $T_{vj} = 25$ °C



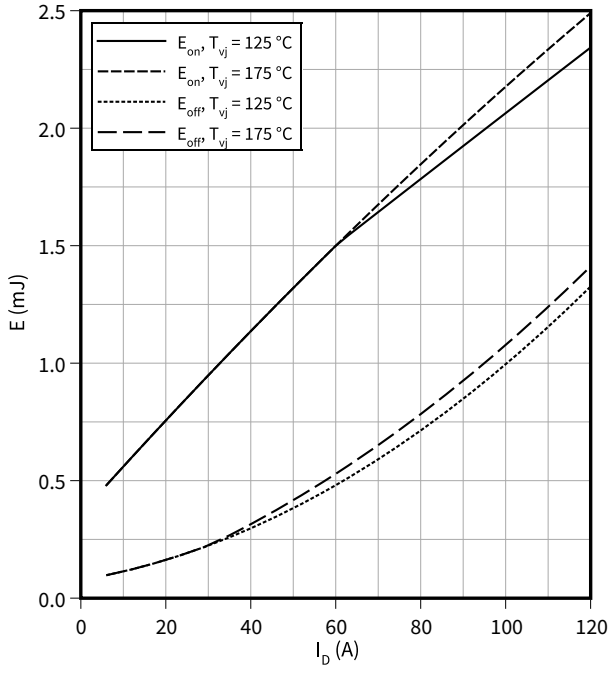
Capacity characteristic (typical), MOSFET

$C = f(V_{DS})$
$f = 100$ kHz, $T_{vj} = 25$ °C, $V_{GS} = 0$ V



Switching losses (typical), MOSFET

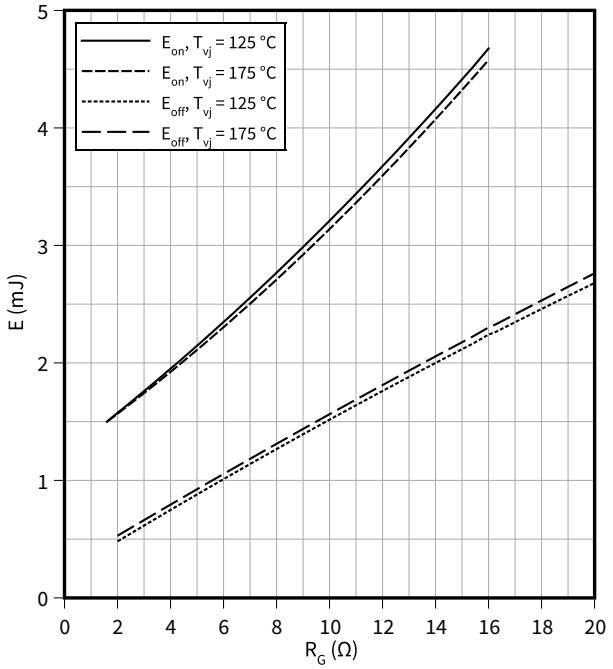
$E = f(I_D)$
$R_{Goff} = 2\ \Omega$, $R_{Gon} = 1.6\ \Omega$, $V_{DD} = 1200$ V, $V_{GS} = -3/18$ V



Switching losses (typical), MOSFET

$E = f(R_G)$

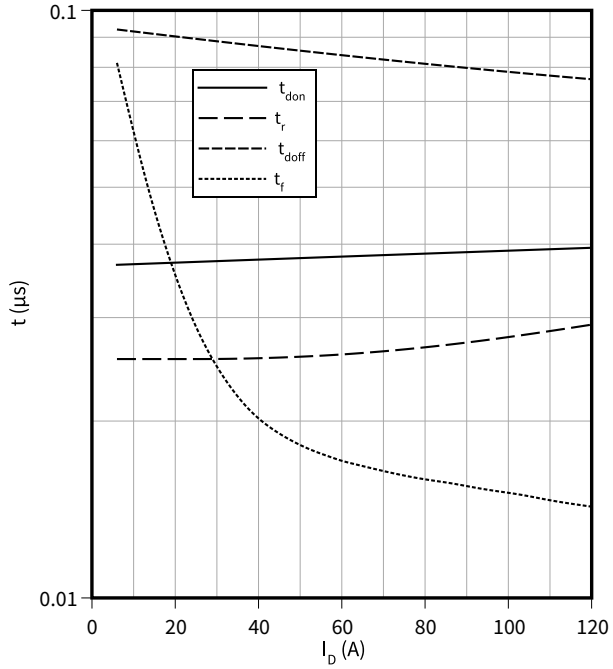
V_{DD} = 1200 V, I_D = 60 A, V_{GS} = -3/18 V



Switching times (typical), MOSFET

$t = f(I_D)$

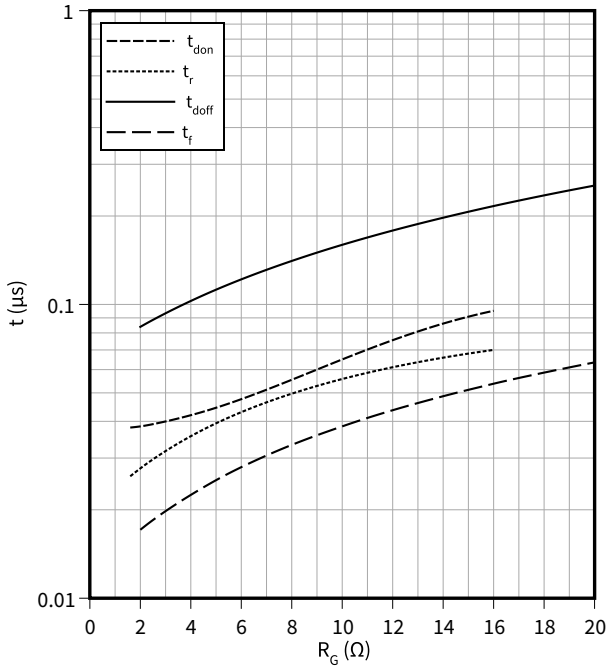
R_{Goff} = 2.0 Ω, R_{Gon} = 1.6 Ω, V_{DD} = 1200 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET

$t = f(R_G)$

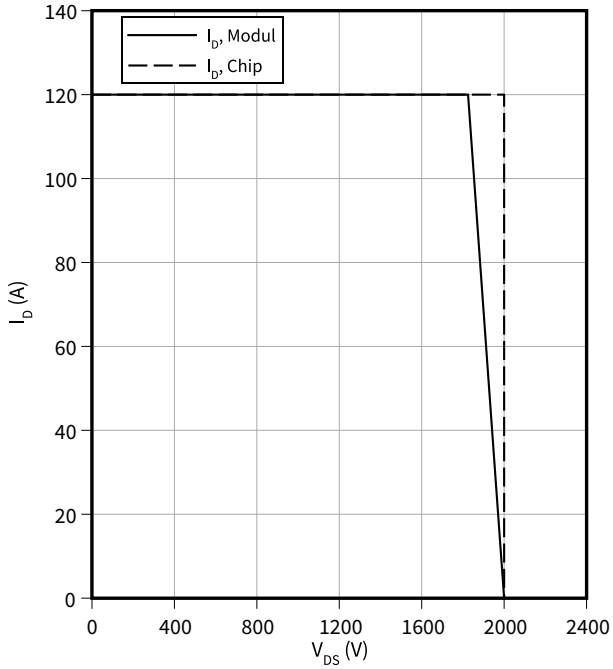
V_{DD} = 1200 V, I_D = 60 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET

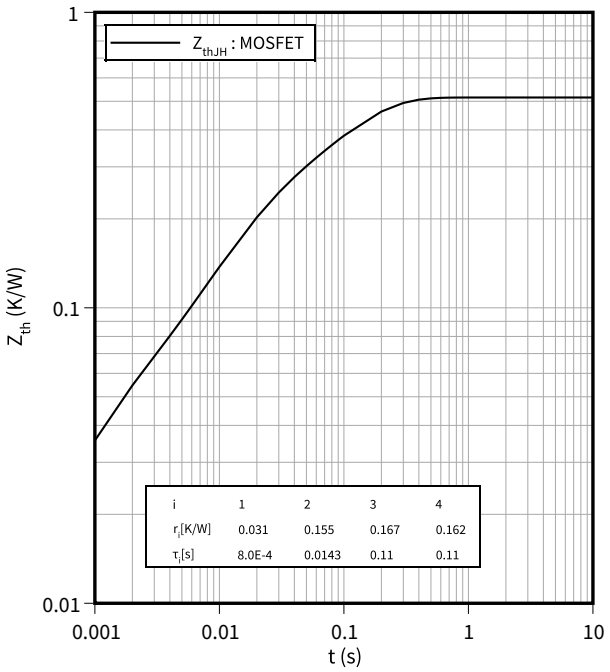
$I_D = f(V_{DS})$

R_{Goff} = 2 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



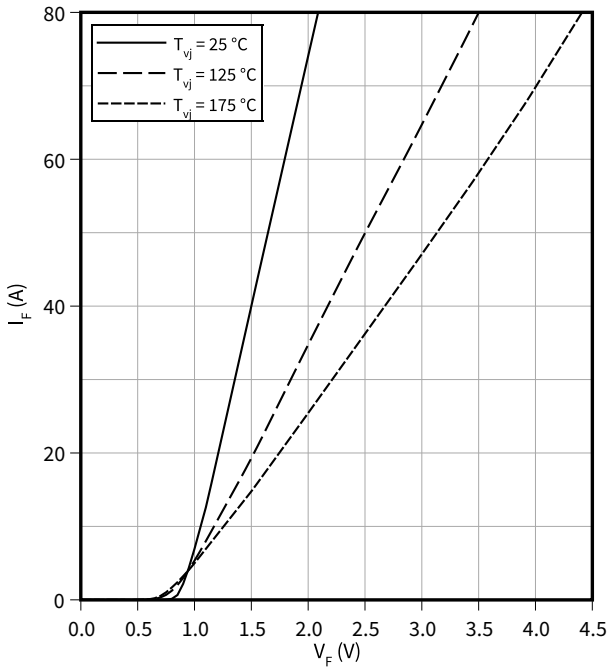
Transient thermal impedance , MOSFET

$Z_{th} = f(t)$



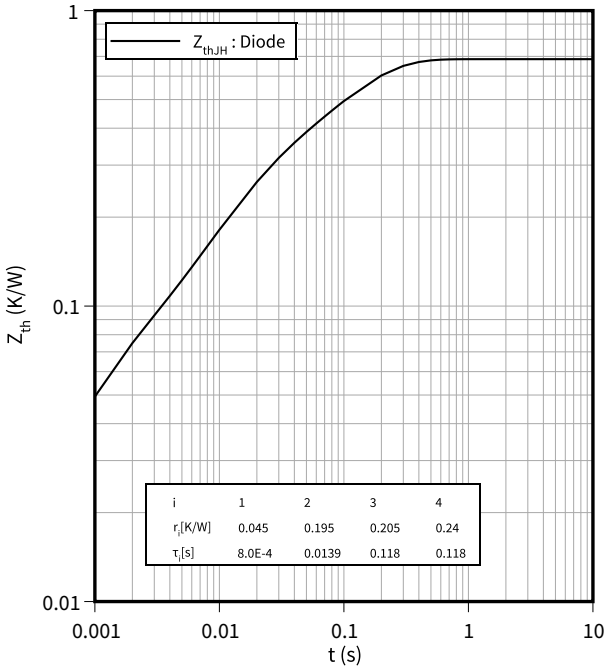
Forward characteristic (typical), Diode, Boost

$I_F = f(V_F)$



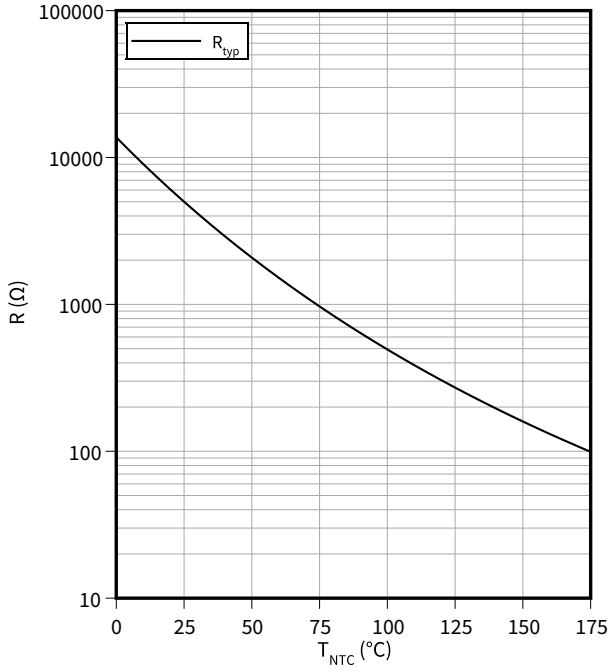
Transient thermal impedance, Diode, Boost

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



7 Circuit diagram

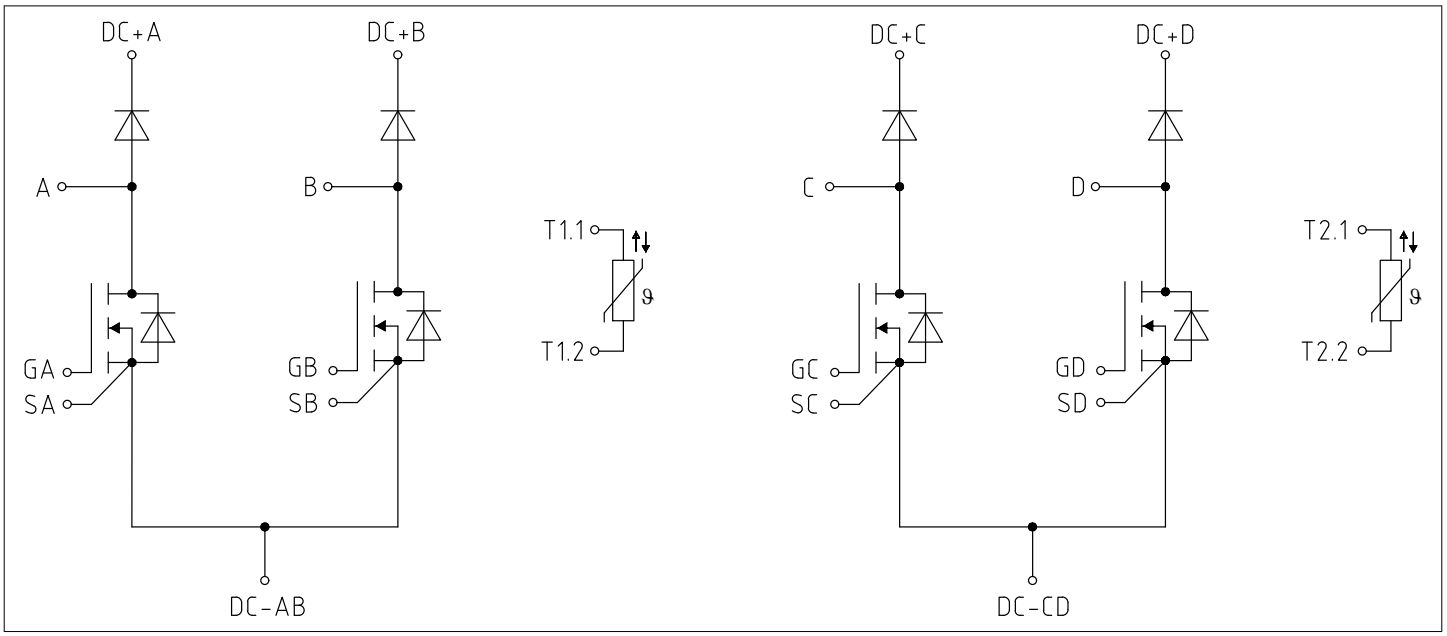


Figure 1

8 Package outlines

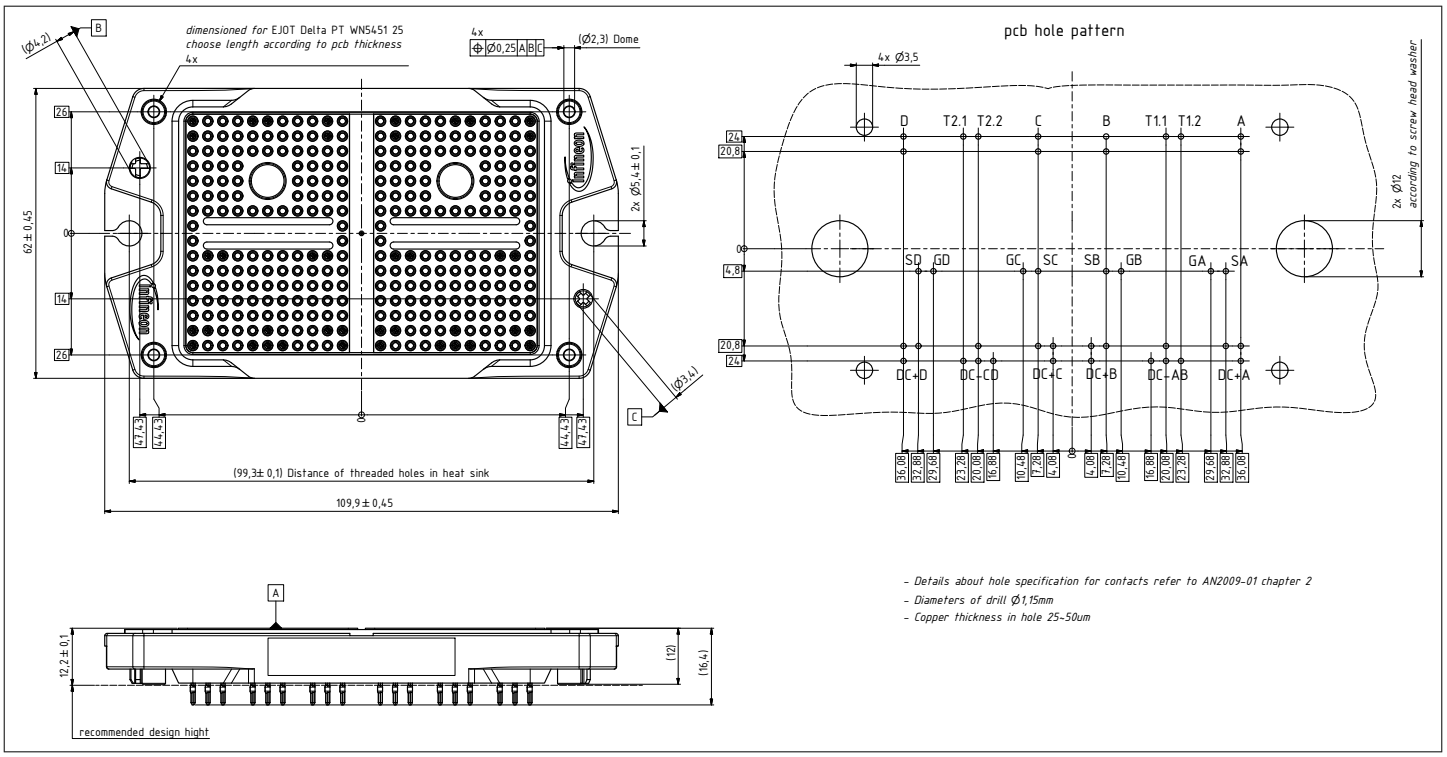


Figure 2

9 Module label code

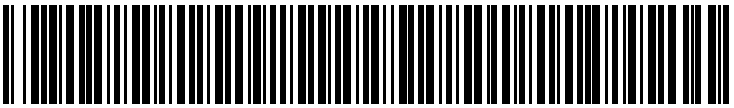
Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	 7154914284655054991530	 7154914284655054991530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2022-07-05	Initial version
1.00	2022-07-15	Final datasheet

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